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ON Semiconductor®

# FQB8N60C / FQI8N60C

## N-Channel QFET® MOSFET

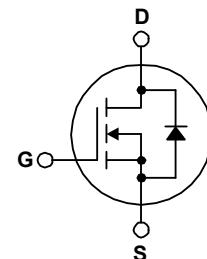
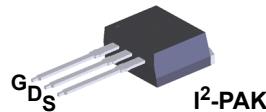
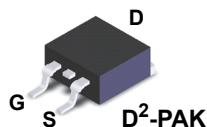
### 600 V, 7.5 A, 1.2 Ω

#### Description

This N-Channel enhancement mode power MOSFET is produced using ON Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### Features

- 7.5 A, 600 V,  $R_{DS(on)} = 1.2 \Omega$  (Max.) @  $V_{GS} = 10$  V,  $I_D = 3.75$  A
- Low Gate Charge (Typ. 28 nC)
- Low  $C_{rss}$  (Typ. 12 pF)
- 100% Avalanche Tested
- RoHS Compliant



#### Absolute Maximum Ratings

 $T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	FQB8N60CTM / FQI8N60CTU	Unit
$V_{DSS}$	Drain-Source Voltage	600	V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ )	7.5	A
	- Continuous ( $T_C = 100^\circ\text{C}$ )	4.6	A
$I_{DM}$	Drain Current - Pulsed	(Note 1)	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	mJ
$I_{AR}$	Avalanche Current	(Note 1)	A
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	(Note 3)	V/ns
$P_D$	Power Dissipation ( $T_A = 25^\circ\text{C}$ )*	3.13	W
	Power Dissipation ( $T_C = 25^\circ\text{C}$ )	147	W
	- Derate above $25^\circ\text{C}$	1.18	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds.	300	$^\circ\text{C}$

#### Thermal Characteristics

Symbol	Parameter	FQB8N60CTM / FQI8N60CTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.85	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Minimum Pad of 2-oz Copper), Max.	62.5	
	Thermal Resistance, Junction to Ambient (*1 in <sup>2</sup> Pad of 2-oz Copper), Max.	40	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQB8N60CTM	FQB8N60C	D <sup>2</sup> -PAK	Tape and Reel	330 mm	24 mm	800 units
FQI8N60CTU	FQI8N60C	I <sup>2</sup> -PAK	Tube	N/A	N/A	50 units

## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_D = 250 \mu\text{A}$	600	--	--	V
$\Delta \text{BV}_{\text{DSS}} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	0.7	--	$\text{V}/^\circ\text{C}$
$I_{\text{DSS}}$	Zero Gate Voltage Drain Current	$V_{\text{DS}} = 600 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$	--	--	1	$\mu\text{A}$
		$V_{\text{DS}} = 480 \text{ V}$ , $T_C = 125^\circ\text{C}$	--	--	10	$\mu\text{A}$
$I_{\text{GSSF}}$	Gate-Body Leakage Current, Forward	$V_{\text{GS}} = 30 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	100	nA
$I_{\text{GSSR}}$	Gate-Body Leakage Current, Reverse	$V_{\text{GS}} = -30 \text{ V}$ , $V_{\text{DS}} = 0 \text{ V}$	--	--	-100	nA

### On Characteristics

$V_{\text{GS(th)}}$	Gate Threshold Voltage	$V_{\text{DS}} = V_{\text{GS}}$ , $I_D = 250 \mu\text{A}$	2.0	--	4.0	V
$R_{\text{DS(on)}}$	Static Drain-Source On-Resistance	$V_{\text{GS}} = 10 \text{ V}$ , $I_D = 3.75 \text{ A}$	--	1.0	1.2	$\Omega$
$g_{\text{FS}}$	Forward Transconductance	$V_{\text{DS}} = 40 \text{ V}$ , $I_D = 3.75 \text{ A}$	--	8.7	--	S

### Dynamic Characteristics

$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}} = 25 \text{ V}$ , $V_{\text{GS}} = 0 \text{ V}$ , $f = 1.0 \text{ MHz}$	--	965	1255	pF
$C_{\text{oss}}$	Output Capacitance		--	105	135	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance		--	12	16	pF

### Switching Characteristics

$t_{\text{d(on)}}$	Turn-On Delay Time	$V_{\text{DD}} = 300 \text{ V}$ , $I_D = 7.5 \text{ A}$ , $R_G = 25 \Omega$	--	16.5	45	ns
$t_r$	Turn-On Rise Time		--	60.5	130	ns
$t_{\text{d(off)}}$	Turn-Off Delay Time		--	81	170	ns
$t_f$	Turn-Off Fall Time		--	64.5	140	ns
$Q_g$	Total Gate Charge	$V_{\text{DS}} = 480 \text{ V}$ , $I_D = 7.5 \text{ A}$ , $V_{\text{GS}} = 10 \text{ V}$	--	28	36	nC
$Q_{\text{gs}}$	Gate-Source Charge		--	4.5	--	nC
$Q_{\text{gd}}$	Gate-Drain Charge		--	12	--	nC

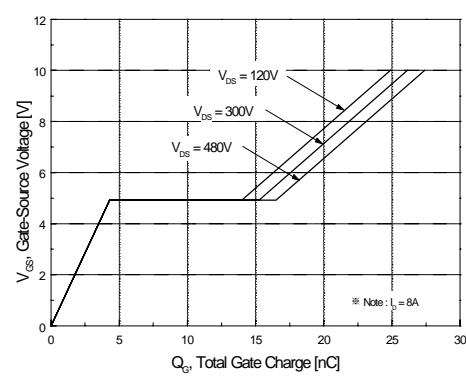
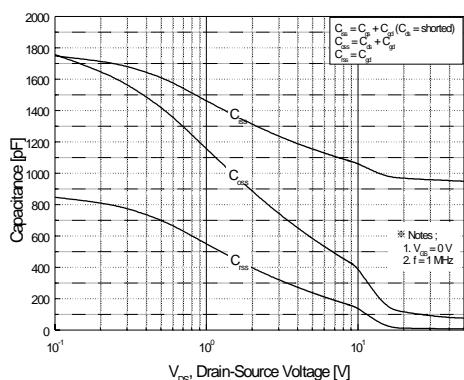
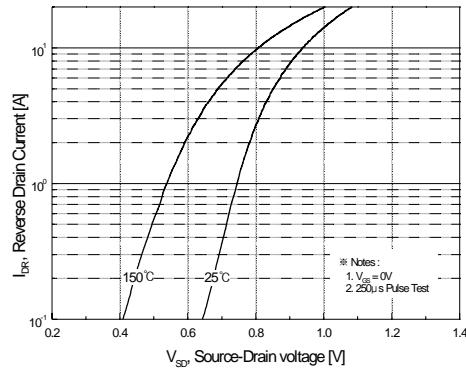
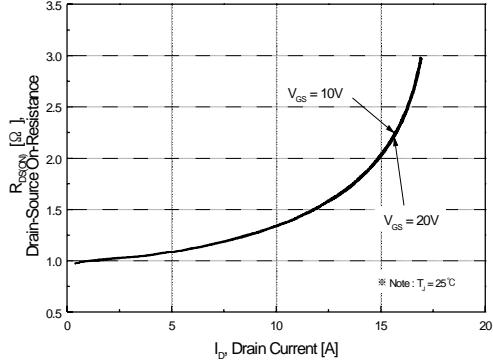
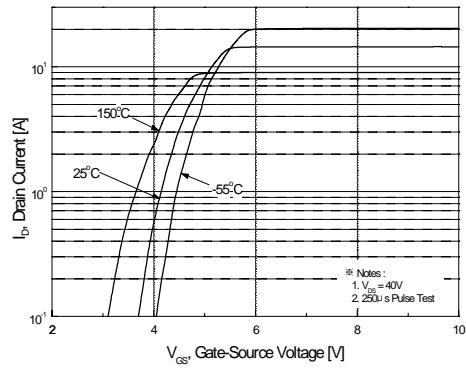
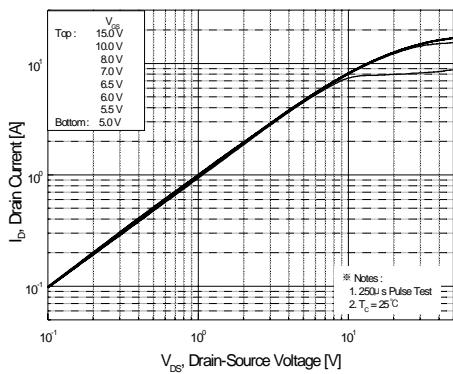
### Drain-Source Diode Characteristics and Maximum Ratings

$I_S$	Maximum Continuous Drain-Source Diode Forward Current	--	--	7.5	A	
$I_{\text{SM}}$	Maximum Pulsed Drain-Source Diode Forward Current	--	--	30	A	
$V_{\text{SD}}$	Drain-Source Diode Forward Voltage	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = 7.5 \text{ A}$	--	--	1.4	V
$t_{\text{rr}}$	Reverse Recovery Time	$V_{\text{GS}} = 0 \text{ V}$ , $I_S = 7.5 \text{ A}$ , $dI_F / dt = 100 \text{ A}/\mu\text{s}$	--	365	--	ns
$Q_{\text{rr}}$	Reverse Recovery Charge		--	3.4	--	$\mu\text{C}$

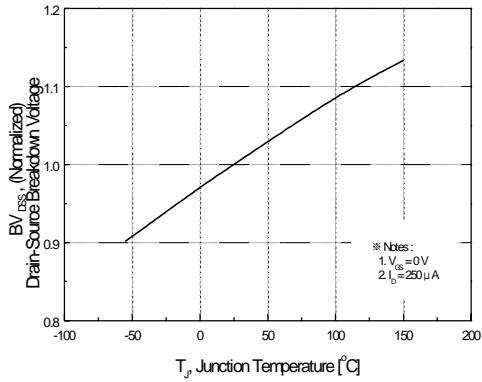
#### Notes:

1. Repetitive rating : pulse-width limited by maximum junction temperature.
2.  $L = 7.3 \text{ mH}$ ,  $I_{AS} = 7.5 \text{ A}$ ,  $V_{DD} = 50 \text{ V}$ ,  $R_G = 25 \Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 7.5 \text{ A}$ ,  $dI/dt \leq 200 \text{ A}/\mu\text{s}$ ,  $V_{DD} \leq \text{BV}_{\text{DSS}}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature.

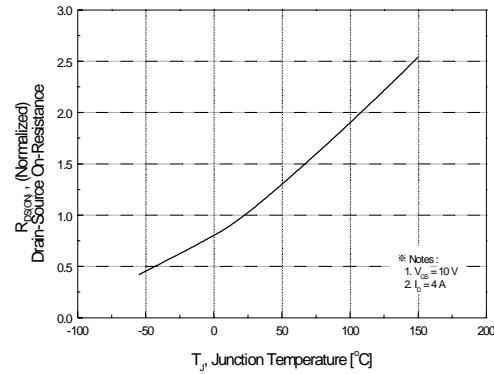
## Typical Characteristics



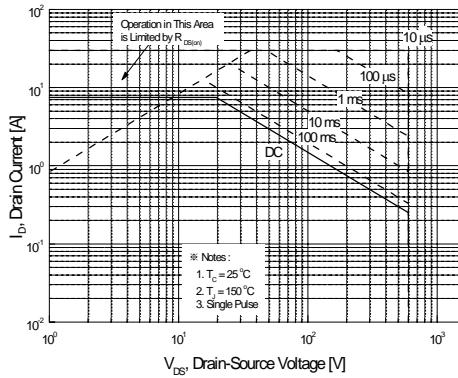
## Typical Characteristics (Continued)



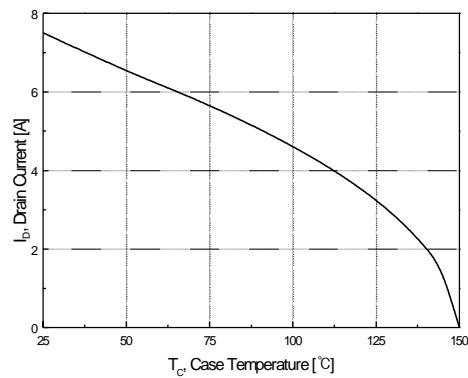
**Figure 7. Breakdown Voltage Variation vs Temperature**



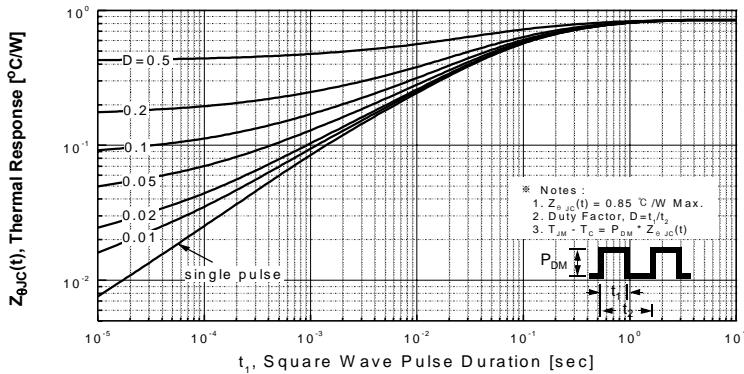
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs Case Temperature**



**Figure 11. Transient Thermal Response Curve**

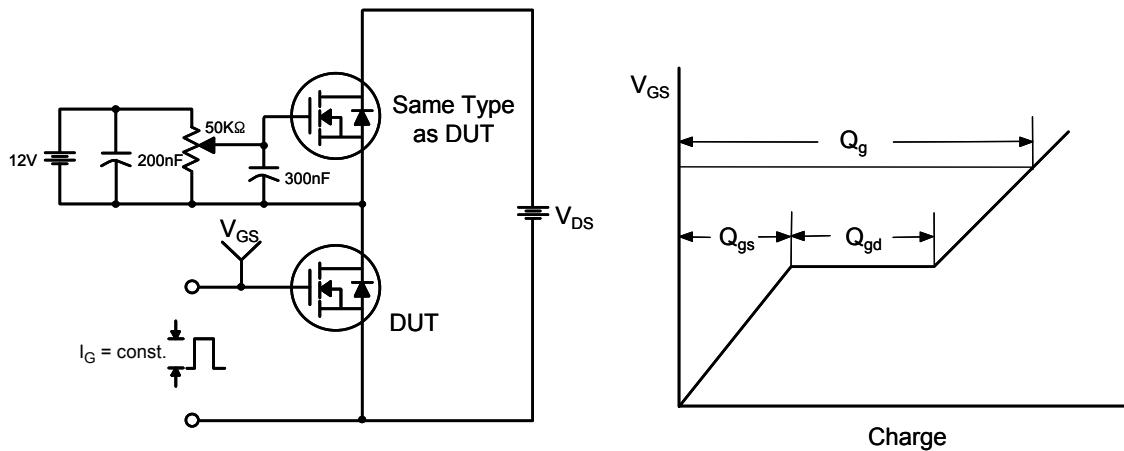


Figure 12. Gate Charge Test Circuit & Waveform

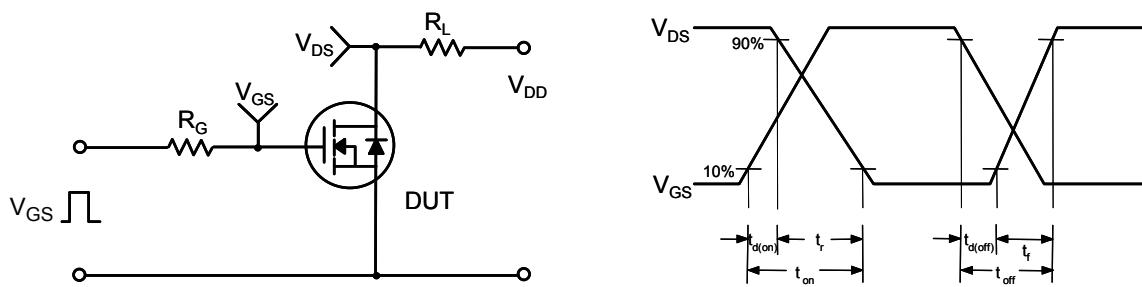


Figure 13. Resistive Switching Test Circuit & Waveforms

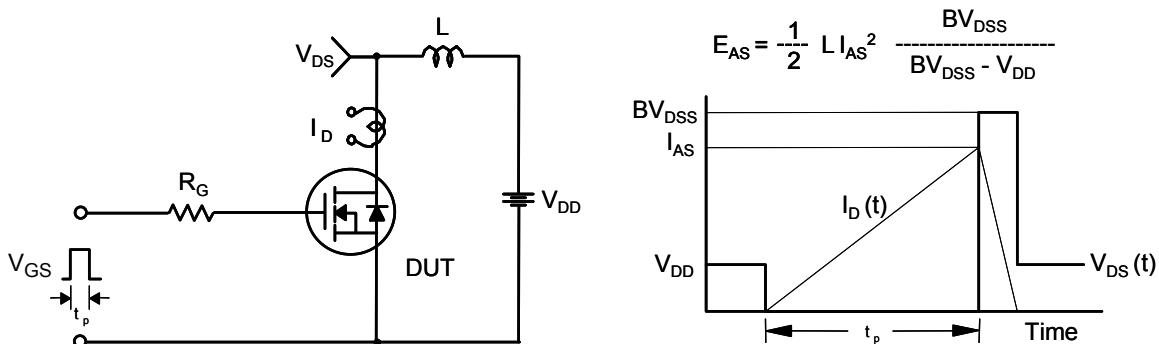


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

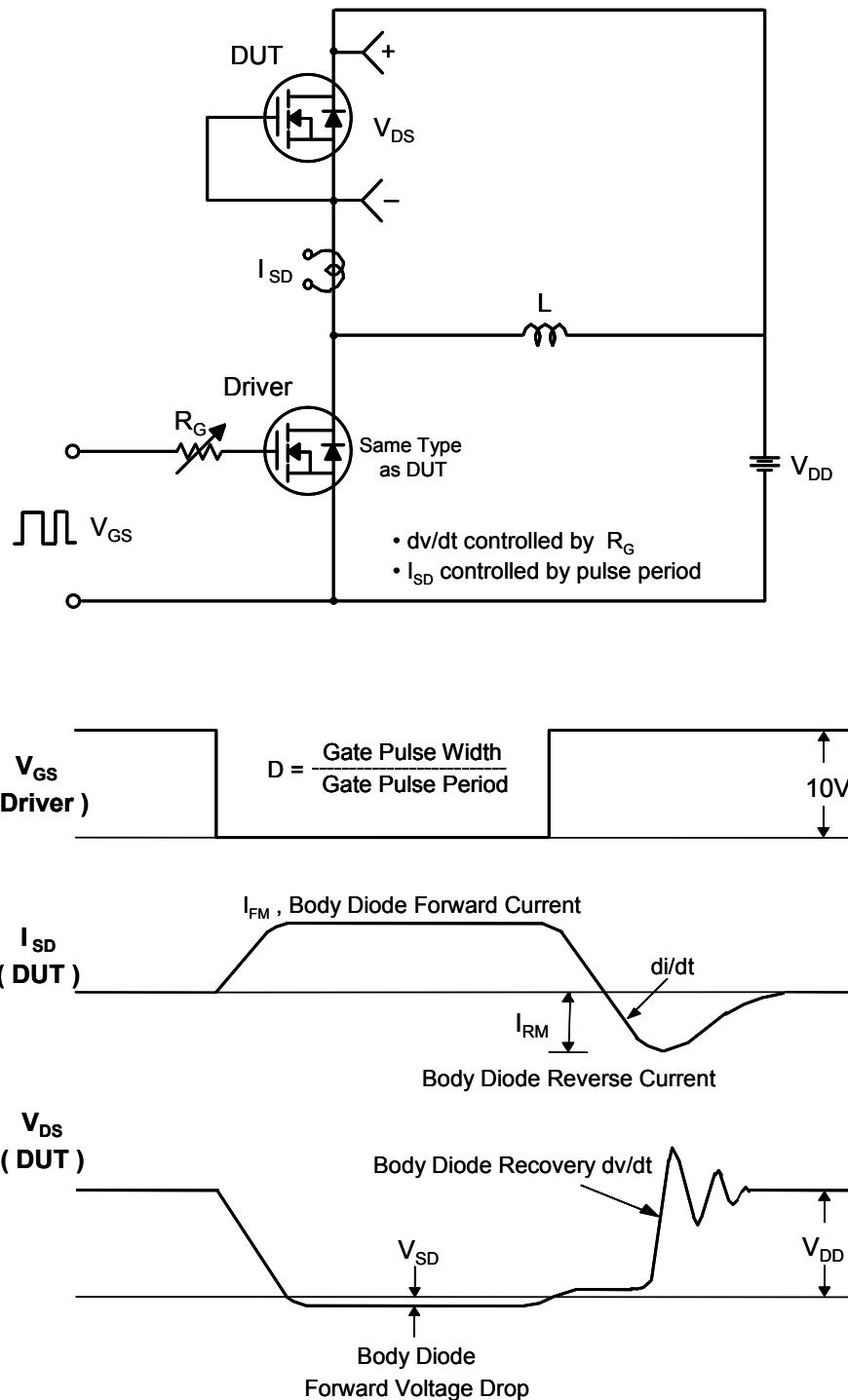
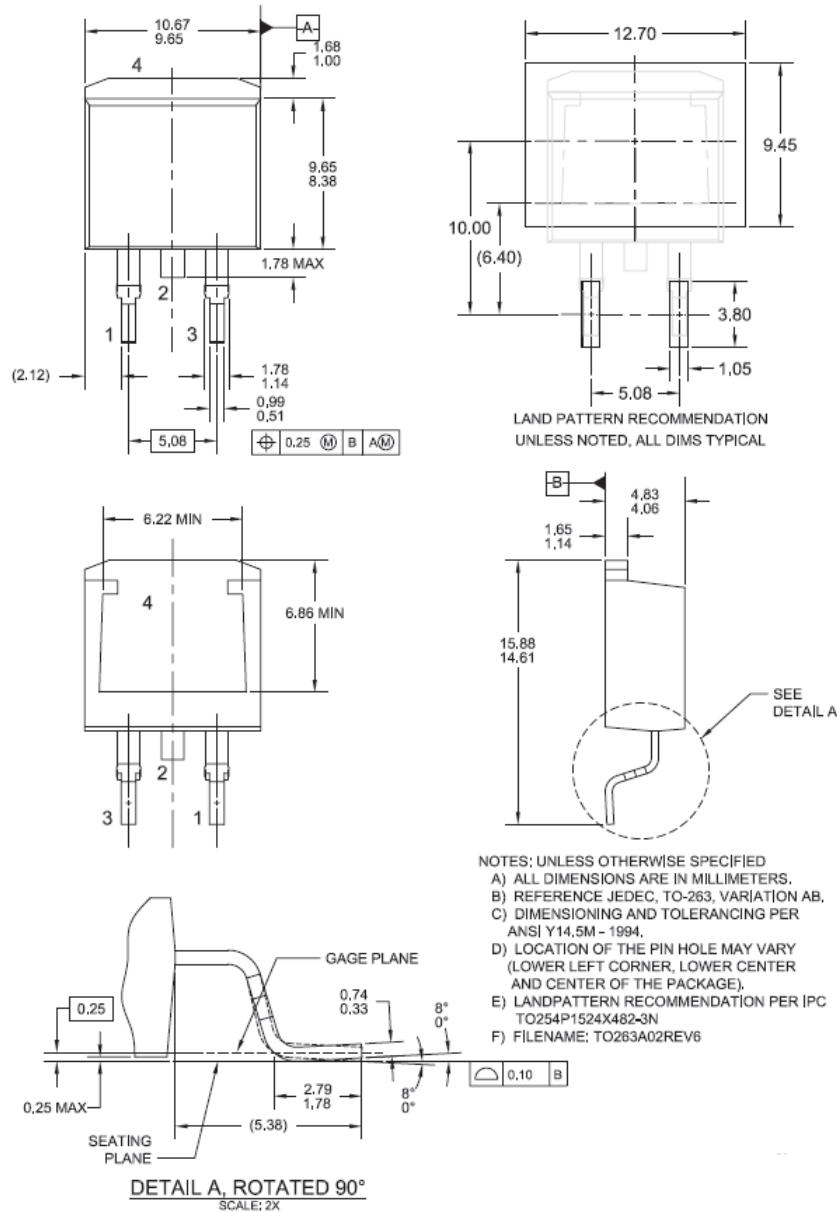


Figure 15. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms

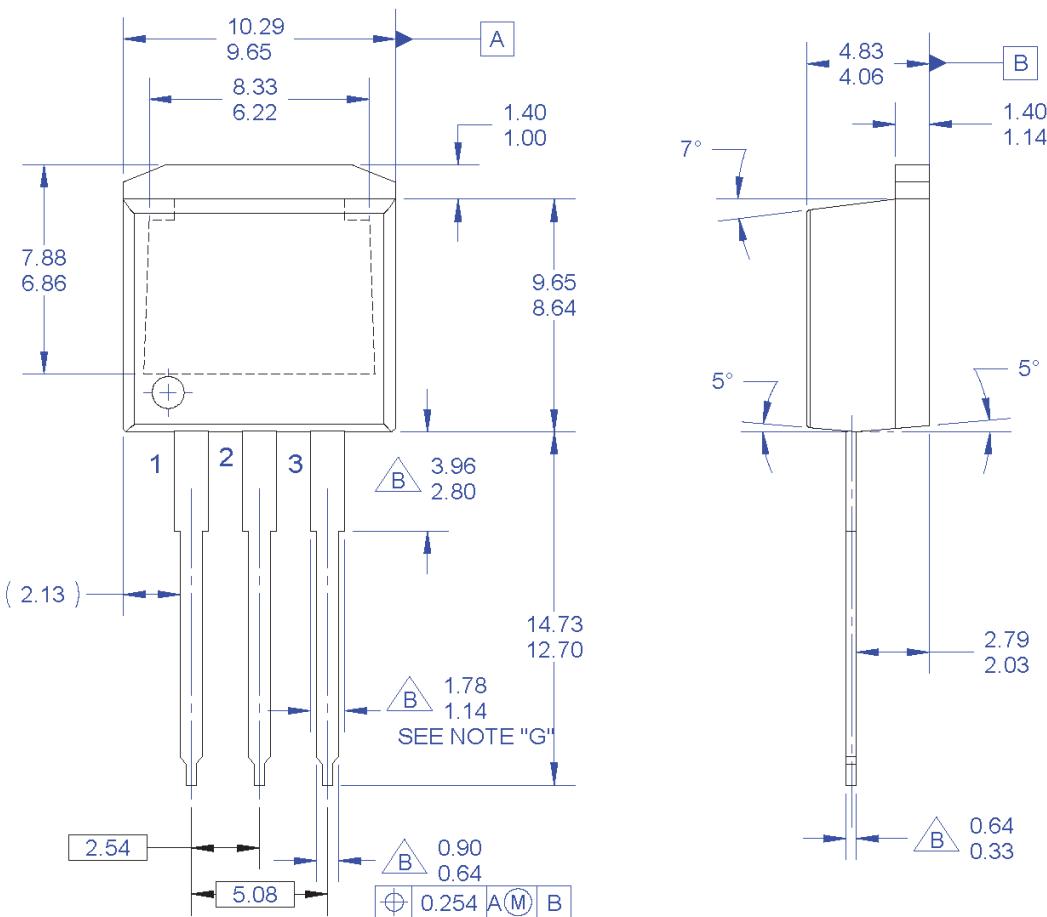
## Mechanical Dimensions



**Figure 16. TO263 (D<sup>2</sup>PAK), Molded, 2-Lead, Surface Mount**

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## Mechanical Dimensions



**Figure 17. TO262 (I<sup>2</sup>PAK), Molded, 3-Lead, Jedec Variation AA**

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